

FEATURES

- 10µs Short Circuit Withstand
- High Thermal Cycling Capability
- Non Punch Through Silicon
- Isolated AISiC Base with AlN Substrates
- Lead Free construction

APPLICATIONS

- High Reliability Inverters
- Motor Controllers
- Traction Drives

The Powerline range of high power modules includes half bridge, chopper, dual, single and bi-directional switch configurations covering voltages from 1200V to 6500V and currents up to 2400A.

The DIM2400ESM12-A000 is a single switch 1200V, n-channel enhancement mode, insulated gate bipolar transistor (IGBT) module. The IGBT has a wide reverse bias safe operating area (RBSOA) plus 10µs short circuit withstand. This device is optimised for traction drives and other applications requiring high thermal cycling capability.

The module incorporates an electrically isolated base plate and low inductance construction enabling circuit designers to optimise circuit layouts and utilise grounded heat sinks for safety.

ORDERING INFORMATION

Order As:

DIM2400ESM12-A000

Note: When ordering, please use the complete part number

KEY PARAMETERS

V_{CES}	1200V
$V_{CE(sat)}$ * (typ)	2.2V
I_C (max)	2400A
$I_{C(PK)}$ (max)	4800A

* Measured at the power busbars, not the auxiliary terminals

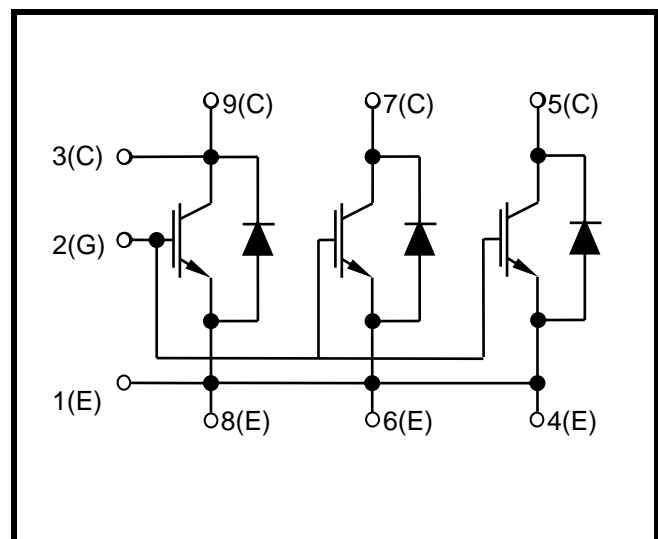
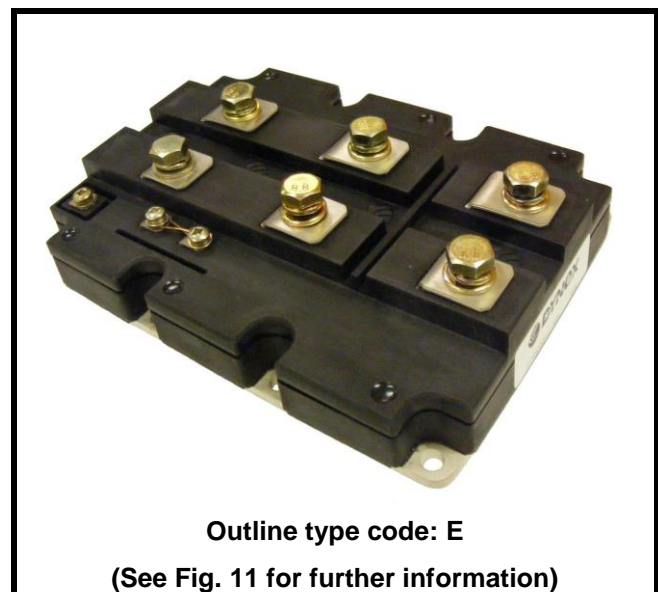


Fig. 1 Circuit configuration



Outline type code: E

(See Fig. 11 for further information)

Fig. 2 Package

ABSOLUTE MAXIMUM RATINGS

Stresses above those listed under 'Absolute Maximum Ratings' may cause permanent damage to the device. In extreme conditions, as with all semiconductors, this may include potentially hazardous rupture of the package. Appropriate safety precautions should always be followed. Exposure to Absolute Maximum Ratings may affect device reliability.

$T_{case} = 25^{\circ}\text{C}$ unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
V_{CES}	Collector-emitter voltage	$V_{GE} = 0V$	1200	V
V_{GES}	Gate-emitter voltage		± 20	V
I_C	Continuous collector current	$T_{case} = 85^{\circ}\text{C}$	2400	A
$I_{C(PK)}$	Peak collector current	1ms, $T_{case} = 115^{\circ}\text{C}$	4800	A
P_{max}	Max. transistor power dissipation	$T_{case} = 25^{\circ}\text{C}$, $T_j = 150^{\circ}\text{C}$	20830	W
I^2t	Diode I^2t value	$V_R = 0$, $t_p = 10\text{ms}$, $T_j = 125^{\circ}\text{C}$	900	kA^2s
V_{isol}	Isolation voltage – per module	Commoned terminals to base plate. AC RMS, 1 min, 50Hz	2500	V
Q_{PD}	Partial discharge – per module	IEC1287, $V_1 = 1300V$, $V_2 = 1000V$, 50Hz RMS	10	pC

THERMAL AND MECHANICAL RATINGS

Internal insulation material:	AlN
Baseplate material:	AlSiC
Creepage distance:	33mm
Clearance:	20mm
CTI (Comparative Tracking Index):	>600

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units
$R_{th(j-c)}$	Thermal resistance – transistor	Continuous dissipation - junction to case	-	-	6	$^{\circ}\text{C}/\text{kW}$
$R_{th(j-c)}$	Thermal resistance – diode	Continuous dissipation - junction to case	-	-	13	$^{\circ}\text{C}/\text{kW}$
$R_{th(c-h)}$	Thermal resistance – case to heatsink (per module)	Mounting torque 5Nm (with mounting grease)	-	-	6	$^{\circ}\text{C}/\text{kW}$
T_j	Junction temperature	Transistor	-	-	150	$^{\circ}\text{C}$
		Diode	-	-	125	$^{\circ}\text{C}$
T_{stg}	Storage temperature range	-	-40	-	125	$^{\circ}\text{C}$
	Screw torque	Mounting – M6	-	-	5	Nm
		Electrical connections – M4	-	-	2	Nm
		Electrical connections – M8	-	-	10	Nm

ELECTRICAL CHARACTERISTICS
 $T_{case} = 25^{\circ}\text{C}$ unless stated otherwise.

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
I_{CES}	Collector cut-off current	$V_{GE} = 0\text{V}, V_{CE} = V_{CES}$			3	mA
		$V_{GE} = 0\text{V}, V_{CE} = V_{CES}, T_{case} = 125^{\circ}\text{C}$			75	mA
I_{GES}	Gate leakage current	$V_{GE} = \pm 20\text{V}, V_{CE} = 0\text{V}$			12	μA
$V_{GE(TH)}$	Gate threshold voltage	$I_C = 120\text{mA}, V_{GE} = V_{CE}$	4.5	5.5	6.5	V
$V_{CE(sat)}$	Collector-emitter saturation voltage	$V_{GE} = 15\text{V}, I_C = 2400\text{A}$		2.2	2.8	V
		$V_{GE} = 15\text{V}, I_C = 2400\text{A}, T_j = 125^{\circ}\text{C}$		2.6	3.3	V
I_F	Diode forward current	DC			2400	A
I_{FM}	Diode maximum forward current	$t_p = 1\text{ms}$			4800	A
V_F	Diode forward voltage	$I_F = 2400\text{A}$		2.1	2.4	V
		$I_F = 2400\text{A}, T_j = 125^{\circ}\text{C}$		2.1	2.4	V
C_{ies}	Input capacitance	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		270		nF
Q_g	Gate charge	$\pm 15\text{V}$		26		μC
C_{res}	Reverse transfer capacitance	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$				nF
L_M	Module inductance			10		nH
R_{INT}	Internal transistor resistance			90		$\mu\Omega$
SC_{Data}	Short circuit current, I_{SC}	$T_j = 125^{\circ}\text{C}, V_{CC} = 900\text{V}$ $t_p \leq 10\mu\text{s}, V_{GE} \leq 15\text{V}$ $V_{CE(max)} = V_{CES} - L^* \times dl/dt$ IEC 60747-9		13500		A

Note:
^{*} L is the circuit inductance + L_M

ELECTRICAL CHARACTERISTICS

$T_{case} = 25^{\circ}\text{C}$ unless stated otherwise

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units	
$t_{d(off)}$	Turn-off delay time	$I_C = 2400\text{A}$ $V_{GE} = \pm 15\text{V}$ $V_{CE} = 600\text{V}$ $R_{G(ON)} = 1.0\Omega$ $R_{G(OFF)} = 1.0\Omega$ $L_S \sim 50\text{nH}$		1370		ns	
t_f	Fall time			230		ns	
E_{OFF}	Turn-off energy loss				520		mJ
$t_{d(on)}$	Turn-on delay time				250		ns
t_r	Rise time				230		ns
E_{ON}	Turn-on energy loss				180		mJ
Q_{rr}	Diode reverse recovery charge	$I_F = 2400\text{A}$ $V_{CE} = 600\text{V}$ $di_F/dt = 9500\text{A}/\mu\text{s}$		310		μC	
I_{rr}	Diode reverse recovery current				1000		A
E_{rec}	Diode reverse recovery energy				150		mJ

$T_{case} = 125^{\circ}\text{C}$ unless stated otherwise

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units	
$t_{d(off)}$	Turn-off delay time	$I_C = 2400\text{A}$ $V_{GE} = \pm 15\text{V}$ $V_{CE} = 600\text{V}$ $R_{G(ON)} = 1.0\Omega$ $R_{G(OFF)} = 1.0\Omega$ $L_S \sim 50\text{nH}$		1570		ns	
t_f	Fall time				230		ns
E_{OFF}	Turn-off energy loss				600		mJ
$t_{d(on)}$	Turn-on delay time				360		ns
t_r	Rise time				290		ns
E_{ON}	Turn-on energy loss				200		mJ
Q_{rr}	Diode reverse recovery charge	$I_F = 2400\text{A}$ $V_{CE} = 600\text{V}$ $di_F/dt = 8500\text{A}/\mu\text{s}$		540		μC	
I_{rr}	Diode reverse recovery current				1260		A
E_{rec}	Diode reverse recovery energy				260		mJ

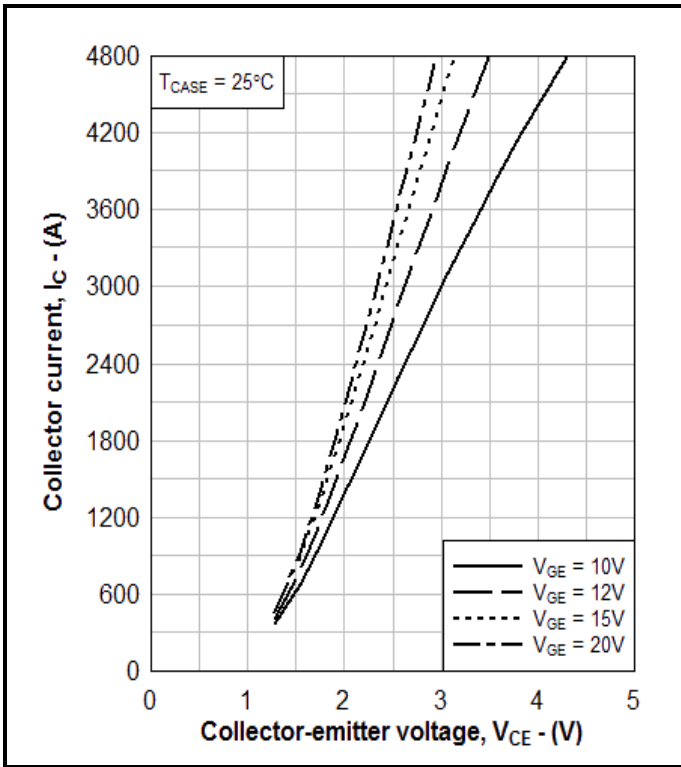


Fig. 3 Typical output characteristics

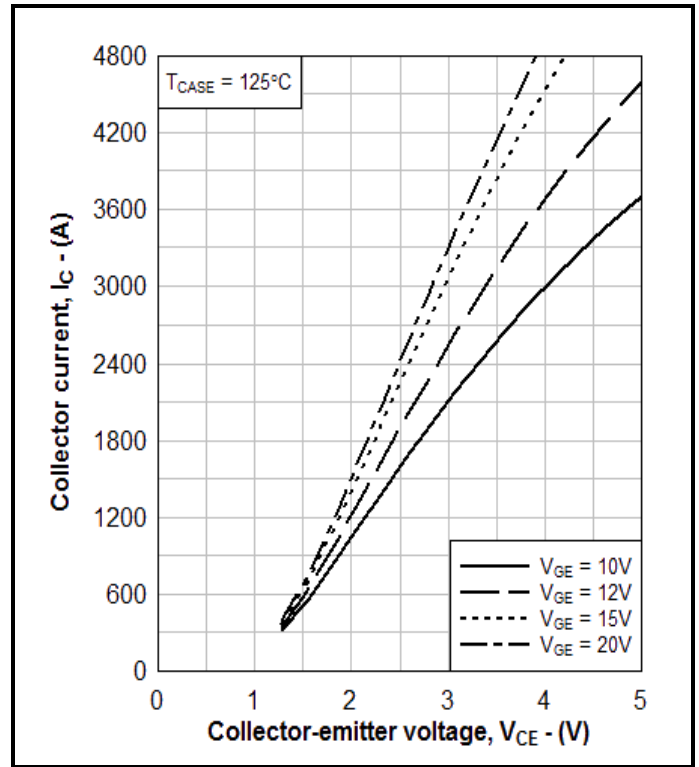


Fig. 4 Typical output characteristics

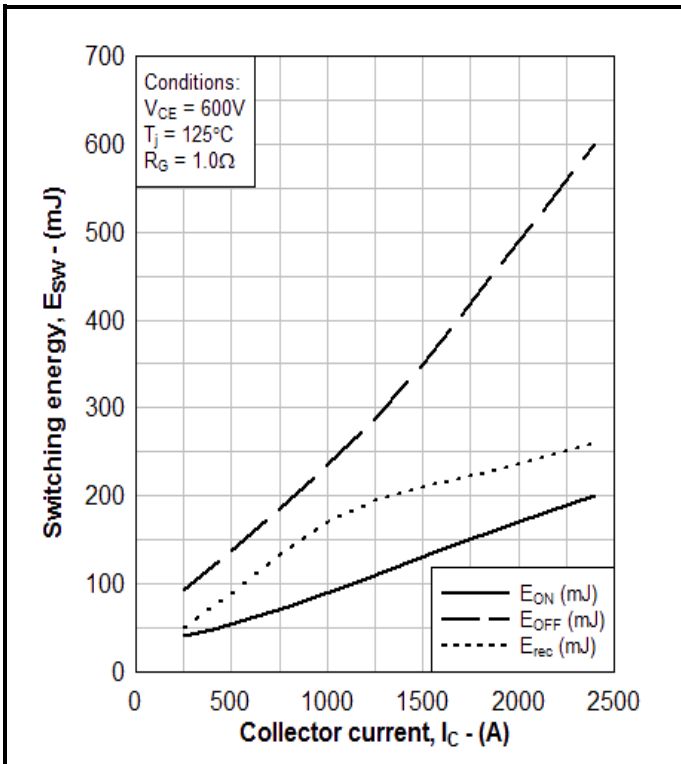


Fig. 5 Typical switching energy vs collector current

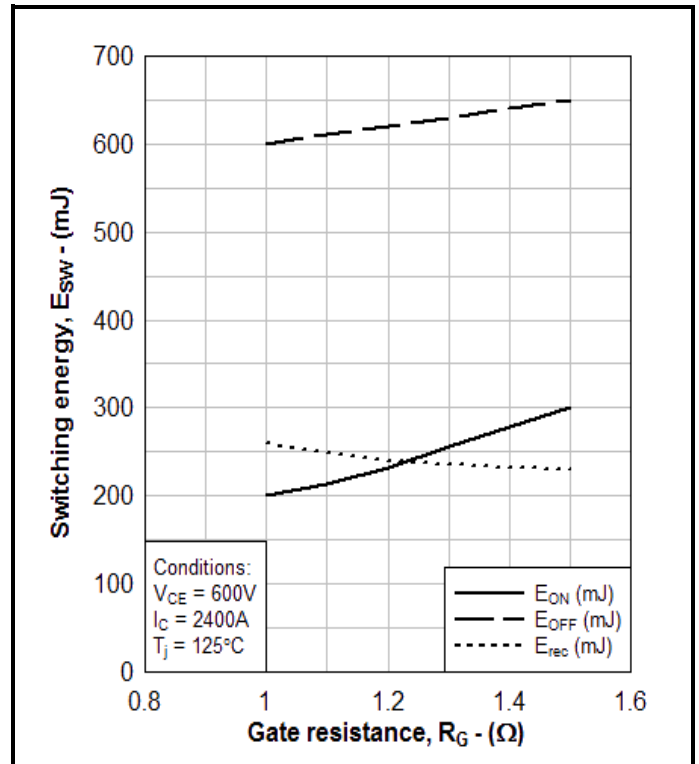


Fig. 6 Typical switching energy vs gate resistance

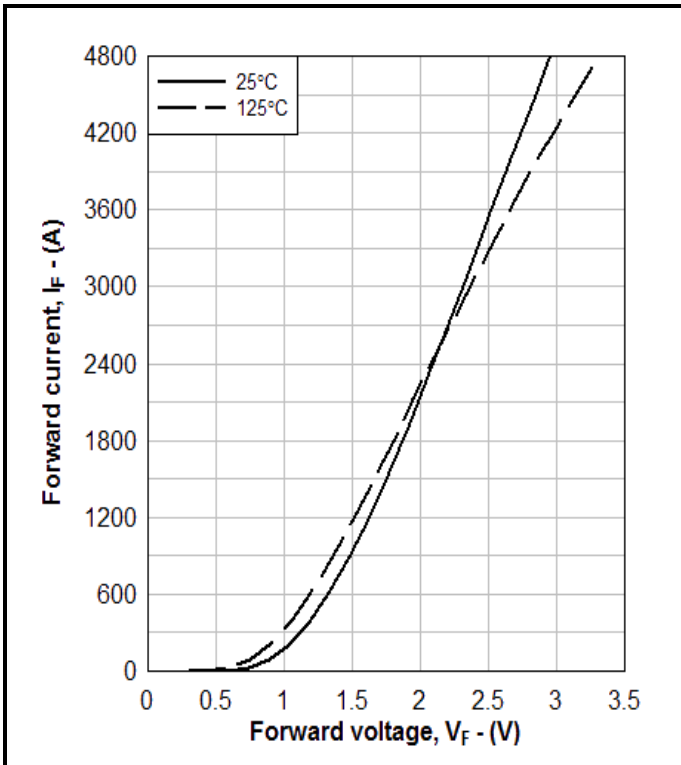


Fig. 7 Diode typical forward characteristics

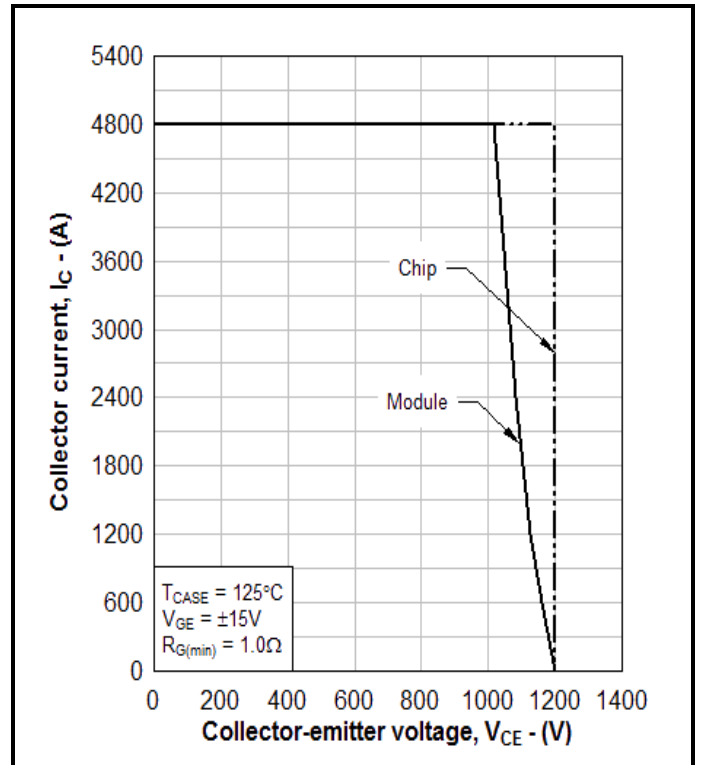


Fig. 8 Reverse bias safe operating area

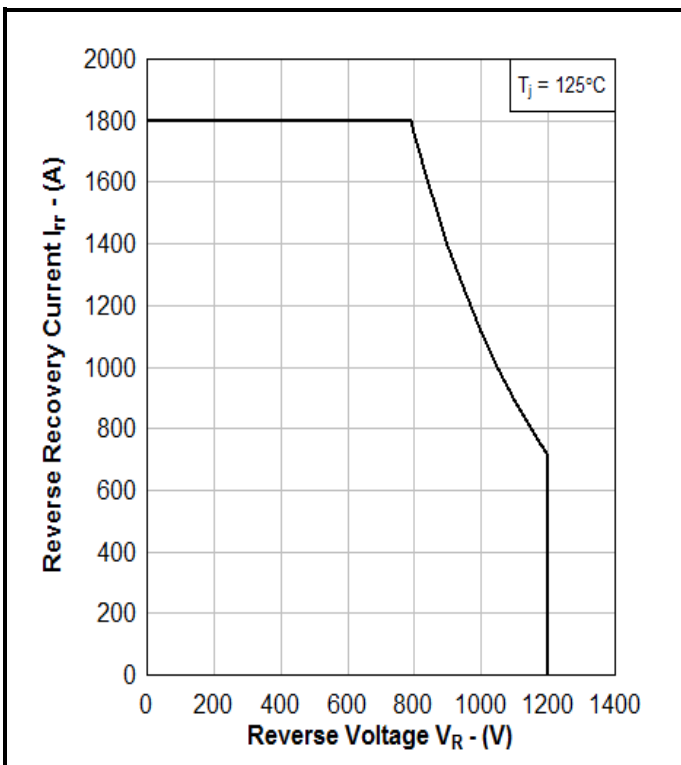


Fig. 9 Diode reverse bias safe operating area

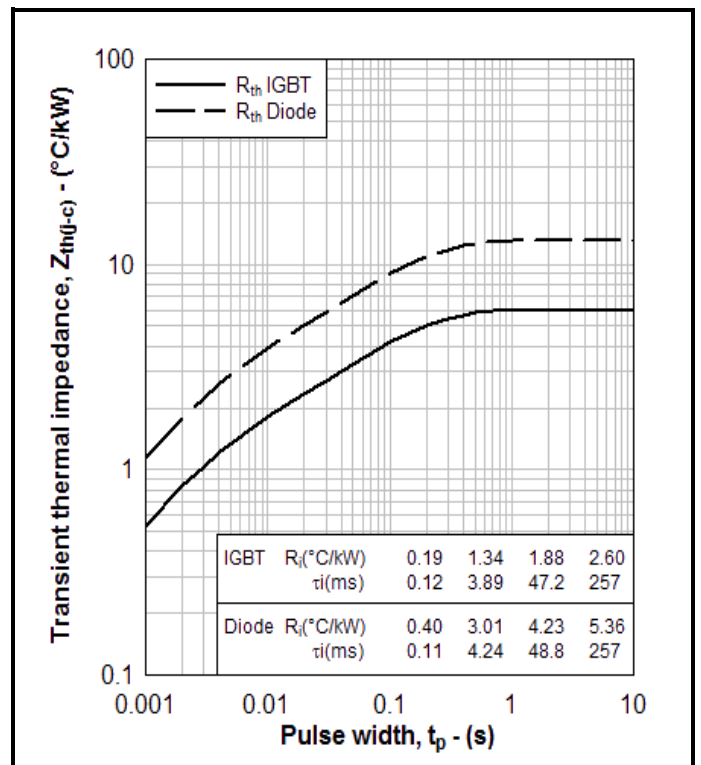
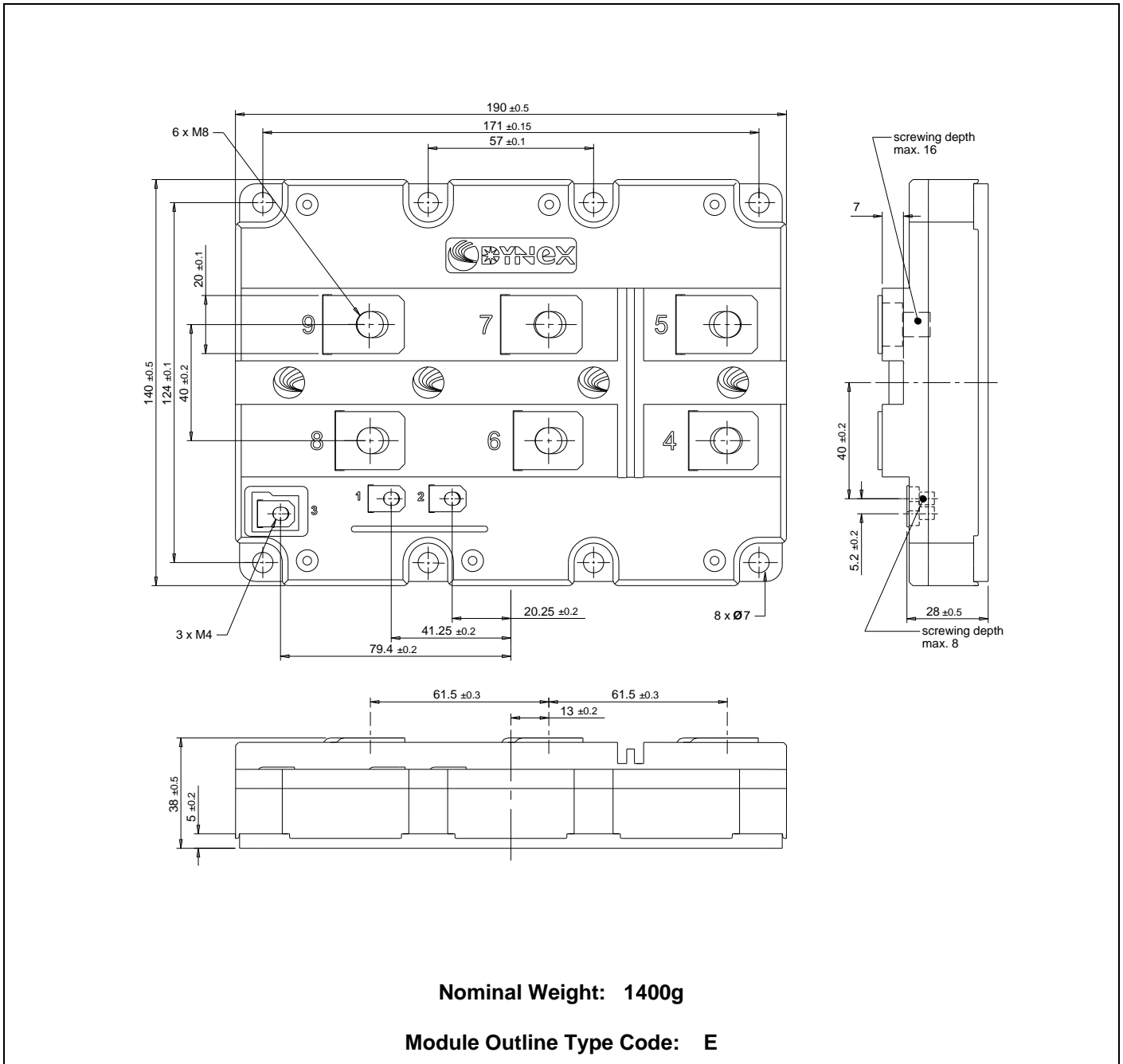


Fig. 10 Transient thermal impedance

PACKAGE DETAILS

For further package information, please visit our website or contact Customer Services.
 All dimensions in mm, unless stated otherwise.
DO NOT SCALE.


Fig. 11 Module outline drawing

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